

Surface Mount Schottky Barrier Diodes

(Pb) Lead(Pb)-Free

Feature:

- * Silicon Epitaxial Planer
- * Low Forward Voltage and Low Reverse Current
- * High Reliability
- * Schottky Barrier Diodes Encapsulated in a SOD-923 Package

Description:

These schottky barrier diodes are designed for high speed switching applications circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

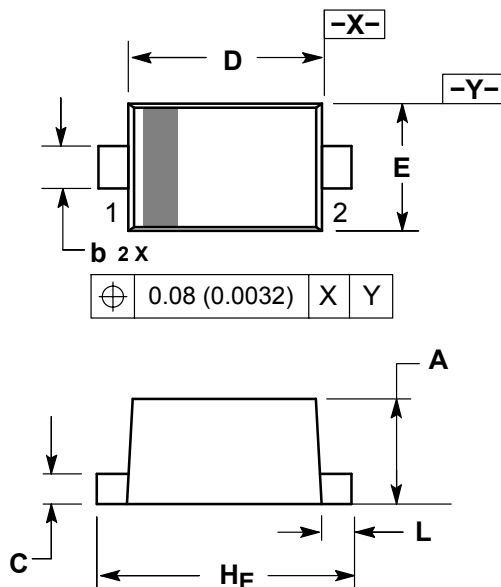
**SMALL SIGNAL
SCHOTTKY DIODES
100m AMPERES
30 VOLTS**



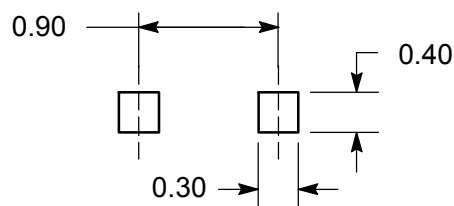
SOD-923

SOD-923 Outline Dimensions

Unit:mm



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.36	0.40	0.43
b	0.15	0.20	0.25
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
HE	0.95	1.00	1.05
L	0.05	0.10	0.15




SOLDERING FOOTPRINT

Maximum Ratings (T_A=25°C Unless otherwise noted)


Characteristic	Symbol	Value	Unit
DC Reverse Voltage	V _R	30	V
Average Rectifier Forward Current	I _O	100	mA
Peak Forward Surge Current ⁽¹⁾	I _{FSM}	500	mA
Thermal Resistance, Junction to Ambient	R _{θJA}	520	°C/W
Power Dissipation	PD	150	mW
Operation Junction Temperature Range	T _J	150	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Electrical Characteristics (T_A=25°C Unless otherwise noted)

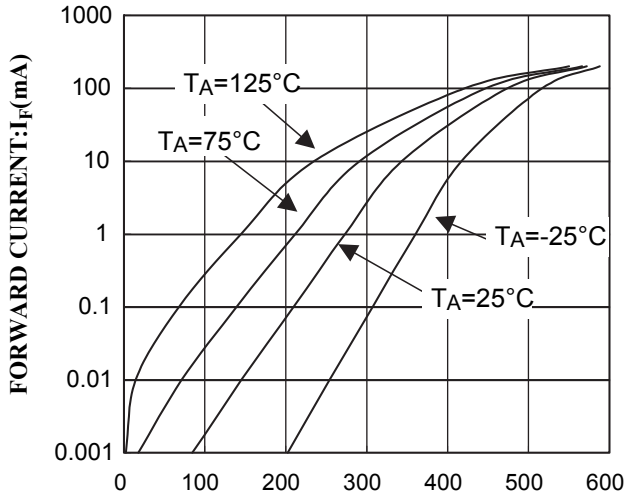
Characteristic	Symbol	Min	Typ	Max	Unit
Forward Voltage I _F =10mA	V _F	-	-	0.45	V
Reverse Leakage V _R =10V	I _R	-	-	0.5	μA

NOTE: 1.60HZ for 1 

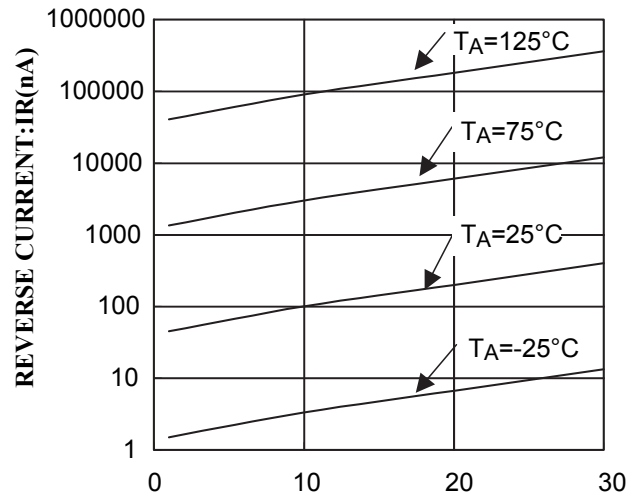
Device Marking

Item	Marking	Equivalent Circuit diagram
WSD520D	E	

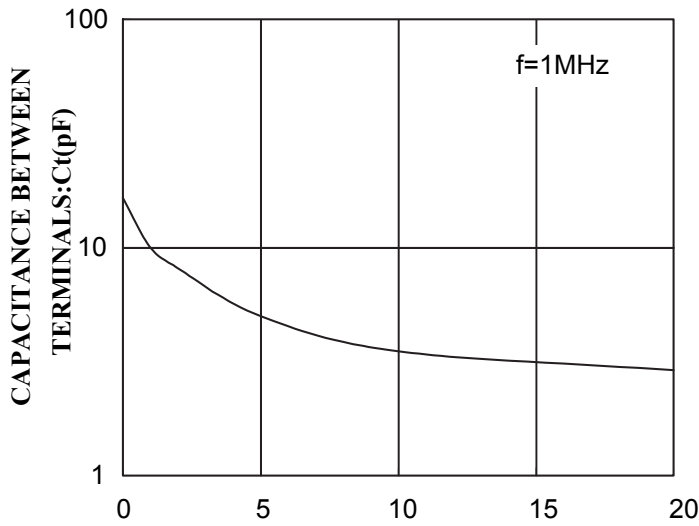
Electrical Characteristic Curves ($T_A=25^\circ\text{C}$)



VF-IF CHARACTERISTICS
Fig.1 FORWARD VOLTAGE : V_F (mV)



VR-IR CHARACTERISTICS
Fig.2 REVERSE VOLTAGE: V_R (V)



VR- C_t CHARACTERISTICS
Fig.3 REVERSE VOLTAGE: V_R (V)